DEVICES INCLUDING FIN TRANSISTORS ROBUST TO GATE SHORTS AND METHODS OF MAKING THE SAME

Abstract

Disclosed are methods, systems and devices, including a method that includes the acts of etching an inter-row trench (144, 220) in a substrate (102, 210), substantially or entirely filling the inter-row trench (144, 220) with a dielectric material (150, 222), and forming a fin (190, 258) and an insulating projection (168, 242) at least in part by etching a gate trench (164, 238) in the substrate (102, 210). In some embodiments, the insulating projection (168, 242) includes at least some of the dielectric material (150, 222) in the inter-row trench (144, 220).

FIG. 26